

General Description

The HSW6822 is the high cell density trench N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The HSW6822 meet the RoHS and Green Product requirement with full function reliability approved.

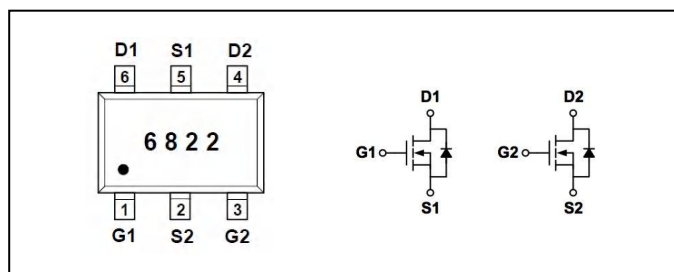
Product Summary

V_{DS}	20	V
$R_{DS(ON),TYP}$	17	mΩ
I_D	5	A

Features

- PWM applications
- Load switch

SOT23-6L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}^1$	5	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}^1$	4	A
I_{DM}	Pulsed Drain Current ²	20	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	1.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	90	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.029	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=4.5V$, $I_D=5A$	---	17	22	$m\Omega$
		$V_{GS}=2.5V$, $I_D=3A$	---	24	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	0.4	0.75	1.2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-2.82	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=20V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=20V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=5A$	---	29	---	S
Q_g	Total Gate Charge (4.5V)	$V_{DS}=10V$, $V_{GS}=4.5V$, $I_D=5A$	---	6.5	---	nC
Q_{gs}	Gate-Source Charge		---	0.9	---	
Q_{gd}	Gate-Drain Charge		---	1.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=10V$, $V_{GS}=4.5V$, $R_G=6\Omega$ $I_D=5A$	---	4	---	ns
T_r	Rise Time		---	21	---	
$T_{d(off)}$	Turn-Off Delay Time		---	16	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	$V_{DS}=10V$, $V_{GS}=0V$, $f=1MHz$	---	480	---	pF
C_{oss}	Output Capacitance		---	69	---	
C_{rss}	Reverse Transfer Capacitance		---	63	---	

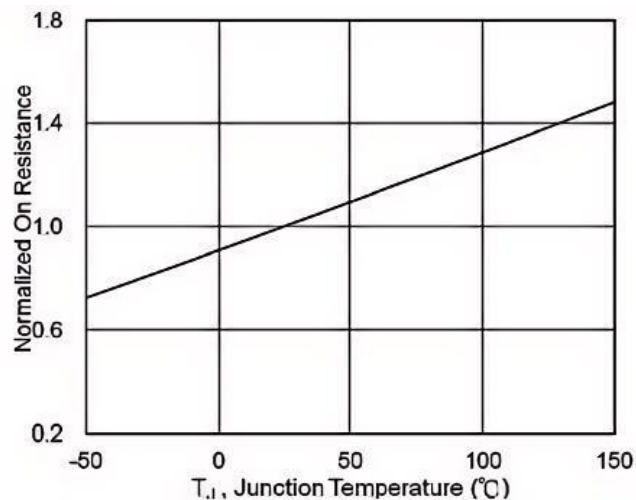
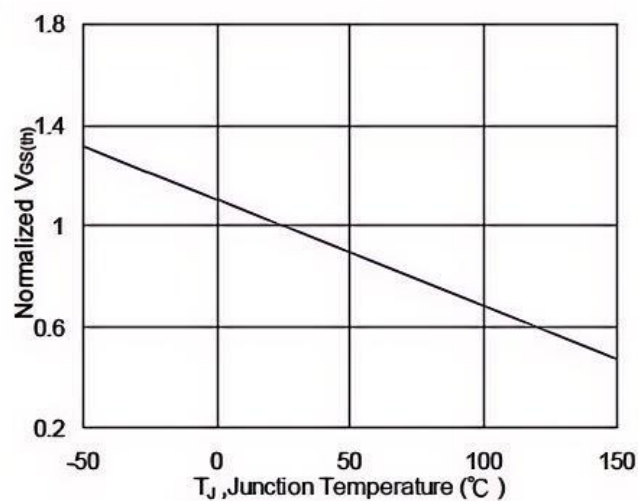
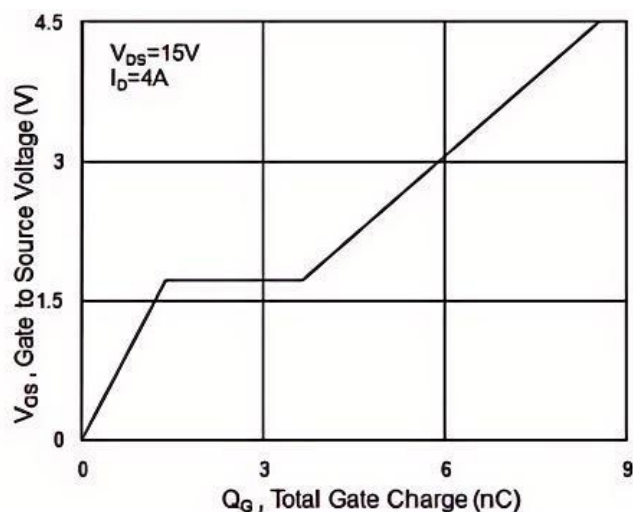
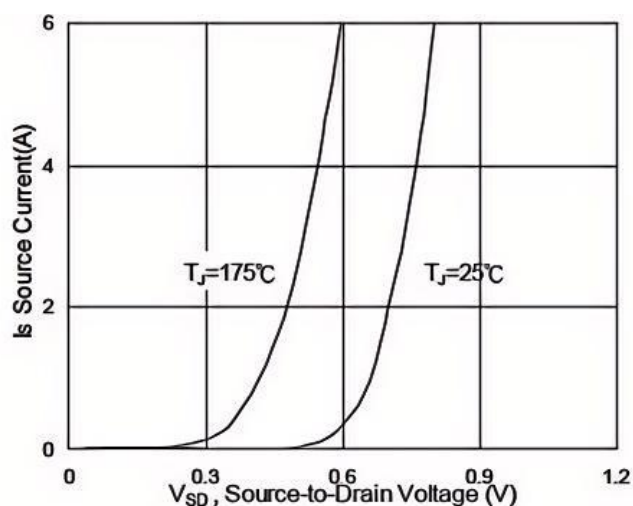
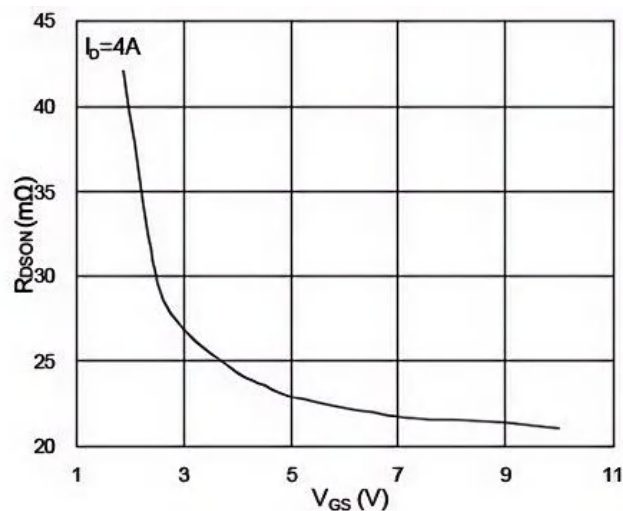
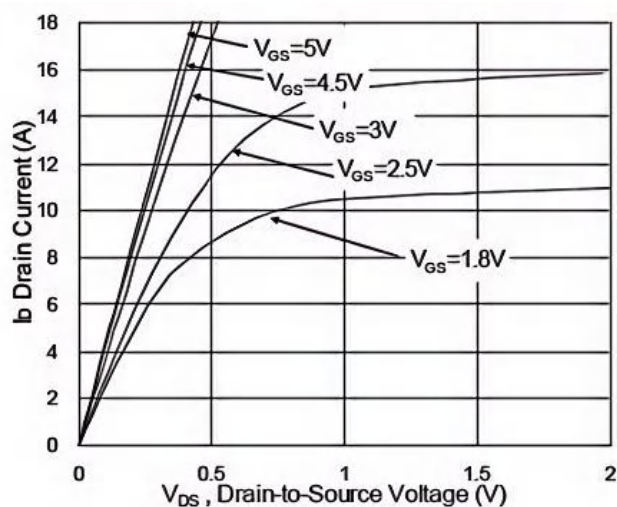
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics





Dual N-CH Fast Switching MOSFETs

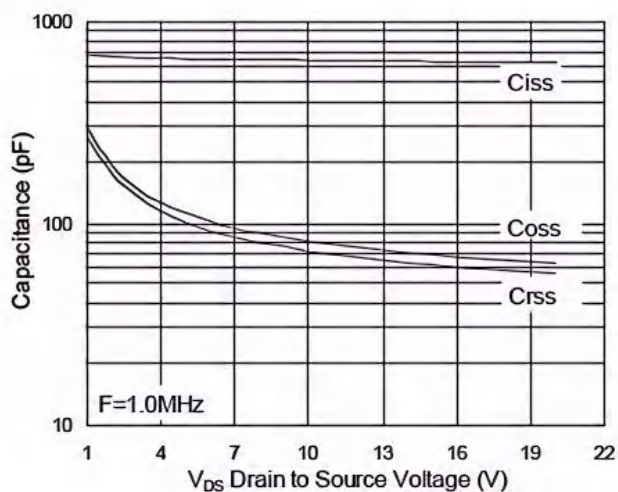


Fig.7 Capacitance

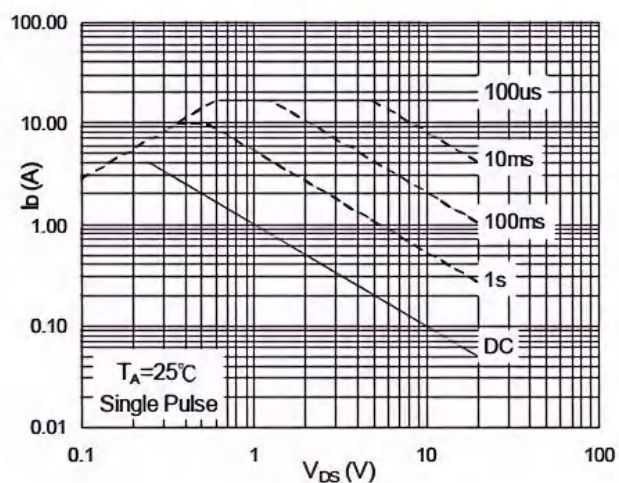


Fig.8 Safe Operating Area

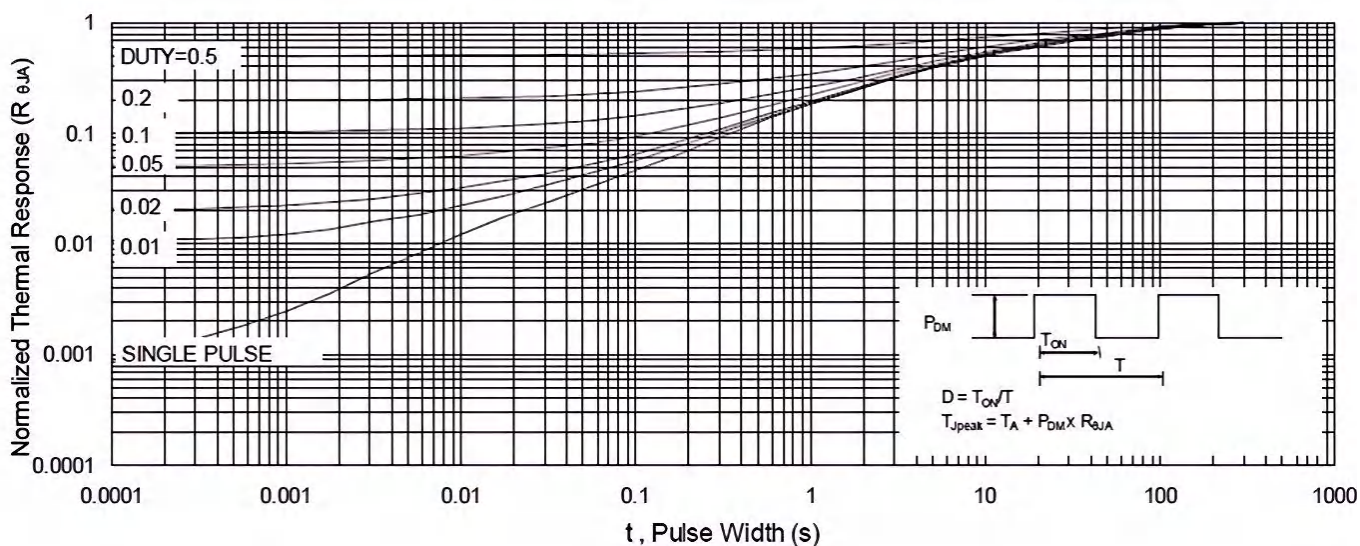


Fig.9 Normalized Maximum Transient Thermal Impedance

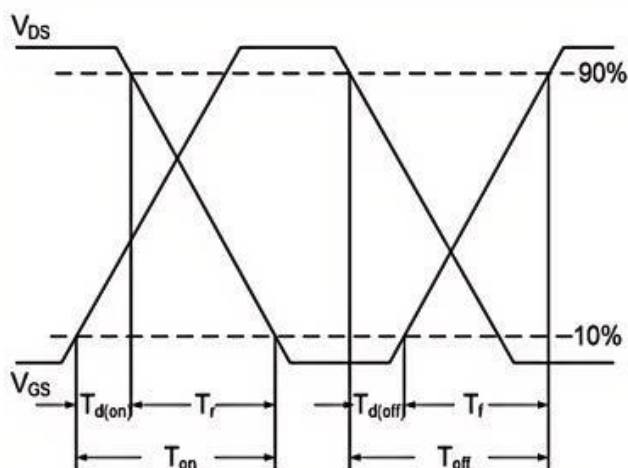


Fig.10 Switching Time Waveform

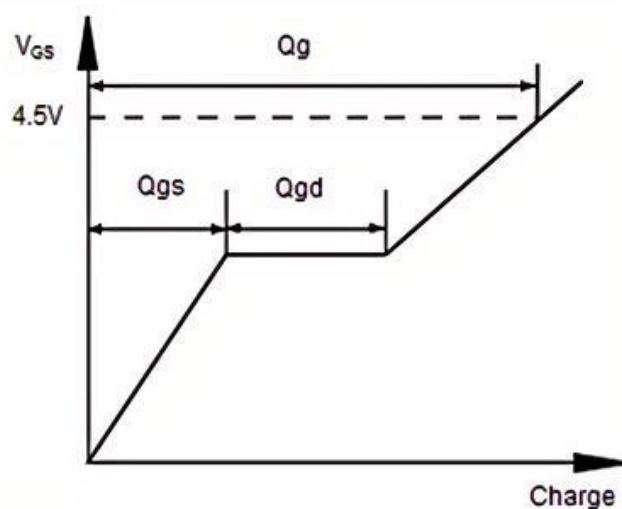
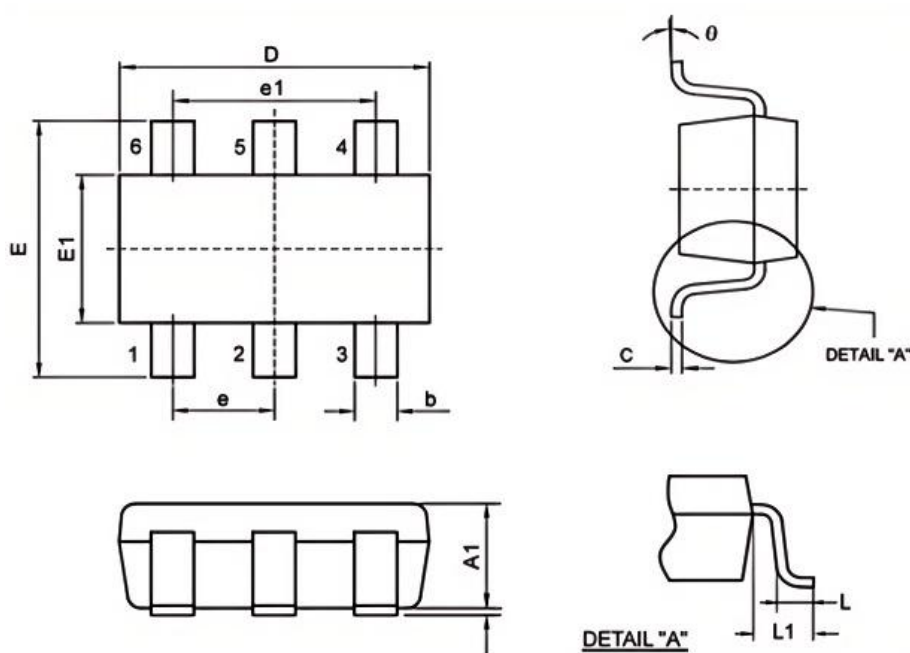


Fig.11 Gate Charge Waveform

Ordering Information

Part Number	Package code	Packaging
HSW6822	SOT23-6L	3000/Tape&Reel

SOT23-6L Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	2.692	3.099	0.106	0.122
E	2.591	3.000	0.102	0.118
E1	1.397	1.803	0.055	0.071
e	0.950 REF.		0.037 REF.	
e1	1.900 REF.		0.075 REF.	
b	0.300	0.500	0.012	0.020
C	0.080	0.200	0.003	0.008
A	0.000	0.100	0.000	0.004
A1	0.700	1.200	0.028	0.048
L	0.300	0.600	0.012	0.024
L1	0.600 REF.		0.023 REF.	
θ	0°	9°	0°	9°



HSW6822 TOP Marking

